Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) An optoelectronic component comprising a semiconductor function region with an active zone and a lateral main direction of extension, wherein said semiconductor function region is provided with at least one opening extending through said active zone in a direction orthogonal to the main direction, and disposed in the region of said opening is a connecting conductor material that is electrically isolated from said active zone at least in a subregion of said opening and that extends entirely through said active zone.

2. (Currently Amended) An optoelectronic component comprising a semiconductor function region with an active zone and a lateral main direction of extension, wherein said semiconductor function region is provided with a lateral side face bounding said active zone, and disposed after said side face in the lateral direction is a connecting conductor material that is electrically isolated from said active zone at least in a subregion of said side face and that extends over an entire length of said active zone in a direction orthogonal to the main direction.

3. (Previously Presented) The optoelectronic component as in claim 1 or 2, wherein said connecting conductor material is at least partially electrically isolated from said active zone by an isolation material.

4. (Previously Presented) The optoelectronic component as in claim 1, wherein said opening is configured as a depression in the lateral direction or said side face is provided with a depression in the lateral direction.

5. (Previously Presented) The optoelectronic component as in claim 1, wherein said isolation material at least partially lines said opening.

6. (Previously Presented) The optoelectronic component as in claim 1, wherein said opening extends in the vertical direction all the way through said semiconductor function region.

7. (Previously Presented) The optoelectronic component as in claim 1 or 2, wherein said semiconductor function region comprises a first main face and a second main face located oppositely from said first main face relative to said active zone, and said semiconductor function region is connected electrically conductively to said connecting conductor material on the side comprising said first main face.

8. (Previously Presented) The optoelectronic component as in claim 7, wherein said connecting conductor material is electrically isolated from said second main face of said semiconductor function region.

9. (Previously Presented) The optoelectronic component as in claim 1, wherein a lateral dimension of said opening is equal to 100 μm or less.

10. (Previously Presented) The optoelectronic component as in claim 1, wherein an envelope forms at least partially around said semiconductor function region.

11. (Previously Presented) The optoelectronic component as in claim 10, wherein said envelope is transparent to a radiation to be generated or received by said active zone.

12. (Previously Presented) The optoelectronic component as in claim 1 or 2, wherein-said active zone is surrounded by an encapsulation that is substantially hermetically tight.

13. (Previously Presented) The optoelectronic component as in claim 1 or 2, wherein said semiconductor function region is disposed on a carrier.

14. (Previously Presented) The optoelectronic component as in claim 13, wherein said connecting conductor material extends to a side of said carrier that is opposite said semiconductor function region.

15. (Previously Presented) The optoelectronic component as in claim 1 or 2, wherein said component can be fabricated in the wafer composite.

16. (Previously Presented) A device comprising a plurality of optoelectronic components as in claim 1 or 2, wherein said semiconductor function regions are disposed at least partially side by side in the lateral direction.

17. (Currently Amended) The device as in claim 16, wherein an envelope forms at least partially around said semiconductor function region, and wherein said envelope is configured in one piece and at least partially forms around said semiconductor function regions.

18. (Previously Presented) The device as in claim 16, wherein said semiconductor function regions are mechanically stabilized by a stabilization layer.

19. (Previously Presented) The device as in claim 18, wherein said envelope is configured as a stabilization layer or part of said stabilization layer.

20. (Previously Presented) The device as in claim 16, wherein said device can be fabricated in the wafer composite.

21. (Withdrawn) A method for producing an optoelectronic component, characterized by the steps of:

a) preparing a wafer composite comprising a semiconductor layer sequence that is disposed on a carrier layer and has an active zone and a lateral main direction of extension;

b) structuring said semiconductor layer sequence such that at least one opening through said active zone is produced or at least one lateral side face bounding said active zone in the lateral direction is formed;

c) disposing a connecting conductor material in the region of said opening or said side face such that said active zone is electrically isolated from said connecting conductor material at least in a subregion of said opening or of said side face;

d) singulation into optoelectronic components whose electrical contacting is effected at least partially via said connecting conductor material.

22. (Withdrawn) The method as in claim 21, wherein said active zone is electrically isolated from said connecting conductor material via an isolation material.

23. (Withdrawn) The method as in claim 21,
wherein said isolation material is disposed in the region of said opening or of said side face.

24. (Withdrawn) The method as in claim 21, wherein at least one depression provided in said semiconductor layer sequence in the lateral direction at least partially surrounds said opening or said opening is configured as a depression in said semiconductor layer sequence in the lateral direction.

25. (Withdrawn) The method as in claim 21, wherein a wall of said opening is at least partially covered with said isolation material or said isolation material is at least partially disposed on said side face.

26. (Withdrawn) The method as in claim 21, wherein said opening extends in the vertical direction all the way through said semiconductor layer sequence.

27. (Withdrawn) The method as in claim 21, wherein said opening is configured as a gap in said semiconductor layer sequence.

28. (Withdrawn) The method as in claim 1, wherein said semiconductor layer sequence is structured such that a plurality of semiconductor function regions is produced.

29. (Withdrawn) The method as in claim 28, wherein said semiconductor function regions are spatially separated from one another by interspaces.

30. (Withdrawn) The method as in claim 28, wherein a plurality of opening through said active zone is produced and a plurality of semiconductor function regions comprises at least one opening through said active zone.

31. (Withdrawn) The method as in claim 28, wherein a plurality of semiconductor function regions each comprise at least one depression in the lateral direction that at least partially surrounds said opening, or, if a plurality of semiconductor function regions is present, the opening is configured as a depression in the lateral direction in the semiconductor function region concerned.

32. (Withdrawn) The method as in claim 28, wherein a plurality of said semiconductor function regions each comprise at least one lateral side face bounding the active zone of the corresponding semiconductor function region.

33. (Withdrawn) The method as in claim 32, wherein said side face bounds the corresponding semiconductor function region in the lateral direction.

34. (Withdrawn) The method as in claim 28, wherein said side face is disposed in the lateral direction after said connecting conductor material, which is electrically isolated from the active zone of said semiconductor function region at least in a subregion of the side face bounding the active zone of said semiconductor function region.

35. (Withdrawn) The method as in claim 21, wherein a first electrical contact is applied to the side of said semiconductor layer sequence facing away from said carrier layer, or to said semiconductor function regions.

36. (Withdrawn) The method as in claim 35, wherein said connecting conductor material is disposed in the region of said opening or of said side face such that an electrically conductive connection is formed between said connecting conductor material and said first contact.

37. (Withdrawn) The method as in claim 35, wherein said opening or said side face is configured such that said first contact can be connected electrically from the side of said semiconductor layer sequence or of said semiconductor function region located oppositely from that comprising said first contact.

38. (Withdrawn) The method as in claim 21, wherein a stabilization layer is disposed after said semiconductor layer sequence or said semiconductor function regions on the side facing away from said carrier layer.

39. (Withdrawn) The method as in claim 38, wherein said stabilization layer is applied to said semiconductor layer sequence or said semiconductor function regions.

40. (Withdrawn) The method as in claim 38, wherein said stabilization layer is disposed after said semiconductor layer sequence or said semiconductor function regions prior to the formation of said opening or said side face.

41. (Withdrawn) The method as in claim 38, wherein said opening or said side face is formed in said semiconductor layer sequence or said semiconductor function regions from the side opposite that comprising said stabilization layer.

42. (Withdrawn) The method as in claim 21, wherein said opening or said side face is formed in said semiconductor layer sequence or said semiconductor function regions from the side opposite that comprising said carrier layer.

43. (Withdrawn) The method as in claim 38, wherein said stabilization layer is disposed after said semiconductor layer sequence or said semiconductor function regions after the creation of said opening or of side face.

44. (Withdrawn) The method as in claim 38, wherein said stabilization layer forms at least partially around said semiconductor function regions.

45. (Withdrawn) The method as in claim 38, wherein said stabilization layer is self-supporting.

46. (Withdrawn) The method as in claim 38, wherein said stabilization layer is transparent to a radiation that is to be generated or received by said active zone.

47. (Withdrawn) The method as in claim 38, wherein said stabilization layer is provided at least in part by spin coating.

48. (Withdrawn) The method as in claim 38, wherein said stabilization layer is provided at least in part by vapor deposition.

49. (Withdrawn) The method as in claim 38, wherein said stabilization layer is disposed after said semiconductor layer sequence or said semiconductor function regions via an adhesion-promoting layer.

50. (Withdrawn) The method as in claim 38, wherein said stabilization layer mechanically stabilizes said semiconductor layer sequence or the structure comprising said semiconductor function regions.

51. (Withdrawn) The method as in claim 21, wherein said carrier layer is at least partially thinned or removed.

52. (Withdrawn) The method as in claim 51, wherein following the thinning or removal of said carrier layer, said semiconductor layer sequence is structured into a plurality of semiconductor function regions.

53. (Withdrawn) The method as in claim 21, wherein said carrier layer is structured according to the arrangement of said semiconductor function regions in such fashion as to produce carrier layer regions that at least partially form a carrier for said semiconductor function region of said optoelectronic component.

54. (Withdrawn) The method as in claim 21, wherein said carrier layer is removed at least in a subregion and said opening or said side face is formed in said semiconductor layer sequence or said semiconductor function regions from the side facing away from said stabilization layer.

55. (Withdrawn) The method as in claim 21, wherein said optoelectronic component is provided with an encapsulation that substantially hermetically tightly surrounds said semiconductor function region.

56. (Withdrawn) The method as in claim 38, wherein said optoelectronic component is provided with an envelope that at least partially envelops or forms around said semiconductor function region, and on singulation said envelope derives at least in part from said stabilization layer.

57. (Withdrawn) The method as in claim 55, wherein said encapsulation comprises said envelope and at least one additional encapsulating element.

58. (Withdrawn) The method as in claim 21, wherein said method is performed on wafer.

59. (Previously Presented) The optoelectronic component as in claim 2, wherein said isolation material is disposed at least partially on said side face.